

Medium-Power Plastic PNP Silicon Transistors

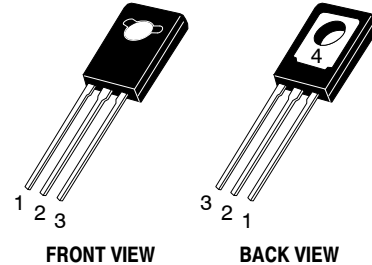
3.0 A, 40–80 V, 30 W
GENERAL PURPOSE
POWER TRANSISTORS

2N4918 - 2N4920 Series

These medium-power, high-performance plastic devices are designed for driver circuits, switching, and amplifier applications.

Features

- Low Saturation Voltage – $V_{CE(sat)} = 0.6 \text{ Vdc (Max) @ } I_C = 1.0 \text{ A}$
- Excellent Power Dissipation, $P_D = 30 \text{ W @ } T_C = 25^\circ\text{C}$
- Excellent Safe Operating Area
- Gain Specified to $I_C = 1.0 \text{ A}$
- Complement to NPN 2N4921, 2N4922, 2N4923
- Pb-Free Package is Available*



TO-225
CASE 077
STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage 2N4918 2N4919 2N4920	V_{CEO}	40 60 80	Vdc
Collector – Base Voltage 2N4918 2N4919 2N4920	V_{CBO}	40 60 80	Vdc
Emitter – Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous (Note 1)	I_C (Note 2)	1.0 3.0	Adc
Base Current	I_B	1.0	Adc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	30 0.24	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The 1.0 A max I_C value is based upon JEDEC current gain requirements. The 3.0 A max value is based upon actual current-handling capability of the device (See Figure 5).
2. Indicates JEDEC Registered Data for 2N4918 Series.

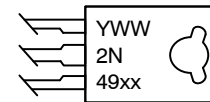
THERMAL CHARACTERISTICS (Note 3)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ_{JC}	4.16	$^\circ\text{C/W}$

3. Recommend use of thermal compound for lowest thermal resistance.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAM



xx = 18, 19, 20
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

2N4918 – 2N4920 Series

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 4) ($I_C = 0.1\text{ Adc}$, $I_B = 0$)	$V_{CEO(sus)}$	40 60 80	– – –	Vdc
Collector Cutoff Current ($V_{CE} = 20\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$)	I_{CEO}	– – –	0.5 0.5 0.5	mAdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CE} = \text{Rated } V_{CEO}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 125^\circ\text{C}$)	I_{CEX}	– –	0.1 0.5	mAdc
Collector Cutoff Current ($V_{CB} = \text{Rated } V_{CB}$, $I_E = 0$)	I_{CBO}	–	0.1	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	1.0	mAdc

ON CHARACTERISTICS

DC Current Gain (Note 4) ($I_C = 50\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 500\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 1.0\text{ Vdc}$)	h_{FE}	40 30 10	– 150 –	–
Collector–Emitter Saturation Voltage (Note 4) ($I_C = 1.0\text{ Adc}$, $I_B = 0.1\text{ Adc}$)	$V_{CE(sat)}$	–	0.6	Vdc
Base–Emitter Saturation Voltage (Note 4) ($I_C = 1.0\text{ Adc}$, $I_B = 0.1\text{ Adc}$)	$V_{BE(sat)}$	–	1.3	Vdc
Base–Emitter On Voltage (Note 4) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 1.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.3	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 250\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ MHz}$)	f_T	3.0	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 100\text{ kHz}$)	C_{ob}	–	100	pF
Small–Signal Current Gain ($I_C = 250\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	25	–	–

4. Pulse Test: $PW \approx 300\ \mu\text{s}$, Duty Cycle $\approx 2.0\%$

ORDERING INFORMATION

Device	Package	Shipping†
2N4920G	TO–225 (Pb–Free)	500 Unit / Bulk

DISCONTINUED (Note 5)

2N4918	TO–225	500 Unit / Bulk
2N4919	TO–225	500 Unit / Bulk
2N4920	TO–225	500 Unit / Bulk

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

5. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

2N4918 - 2N4920 Series

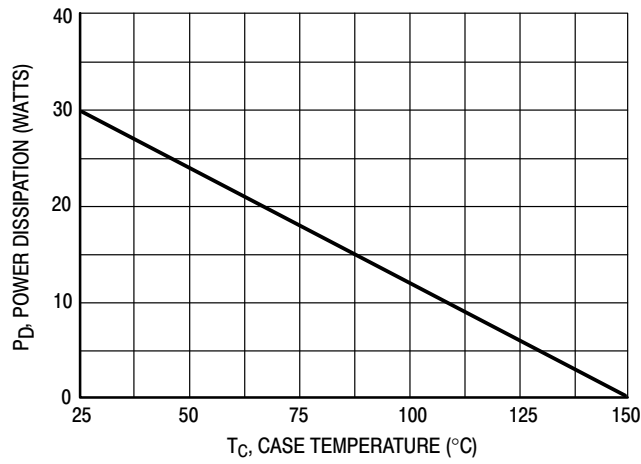


Figure 1. Power Derating

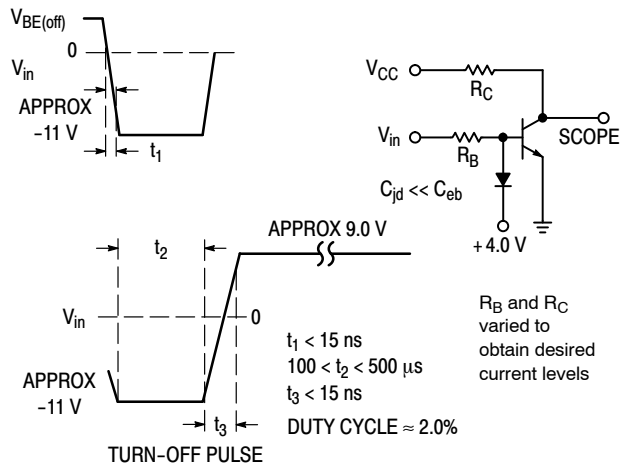


Figure 2. Switching Time Equivalent Test Circuit

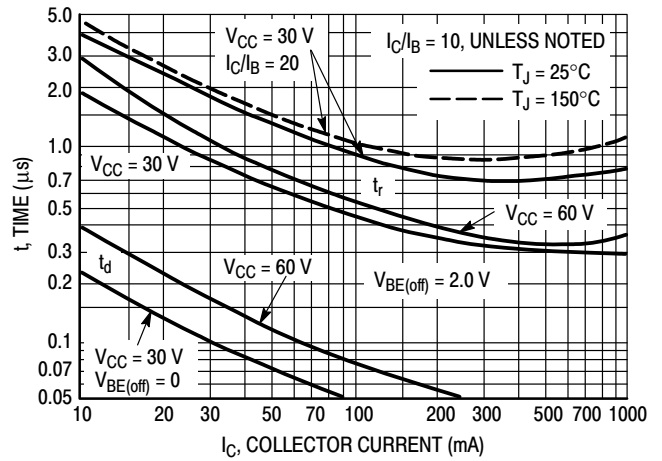


Figure 3. Turn-On Time

2N4918 - 2N4920 Series

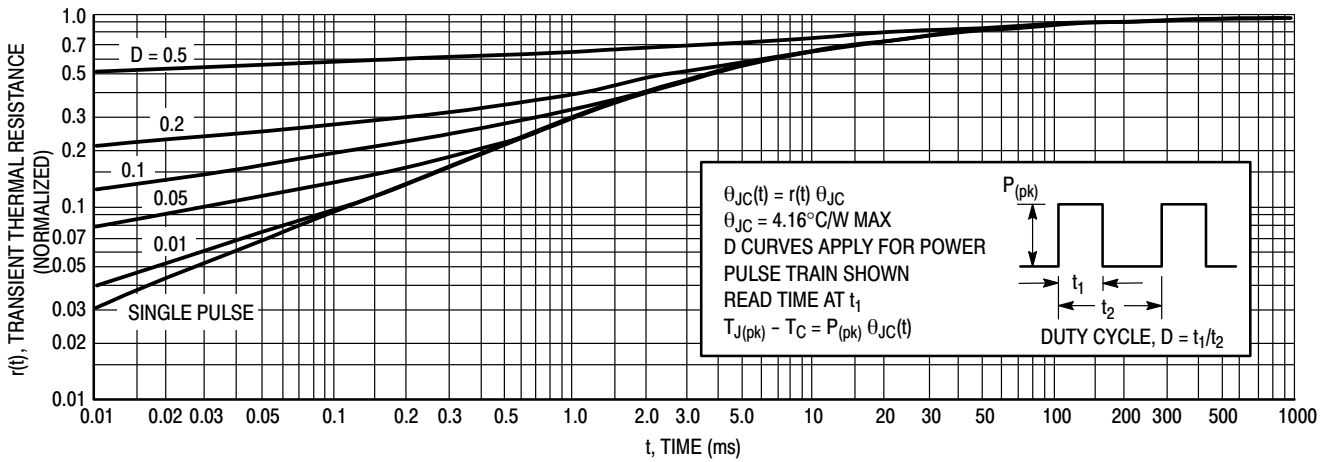


Figure 4. Thermal Response

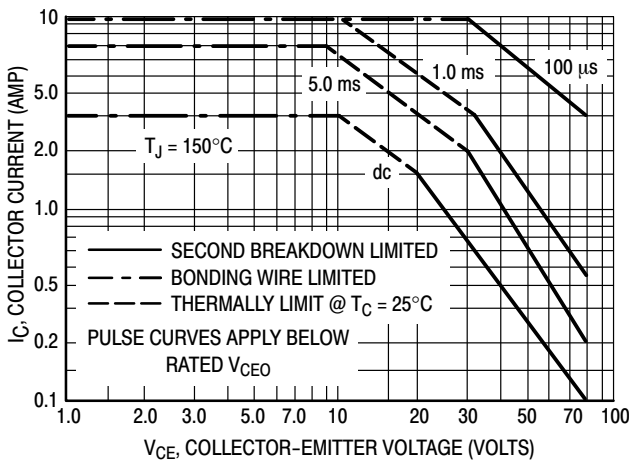


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

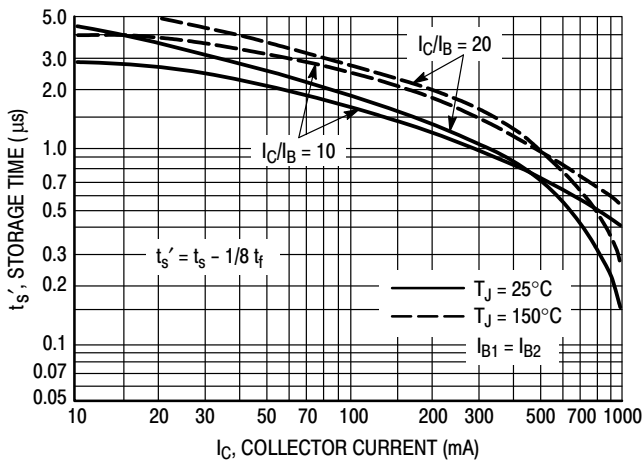


Figure 6. Storage Time

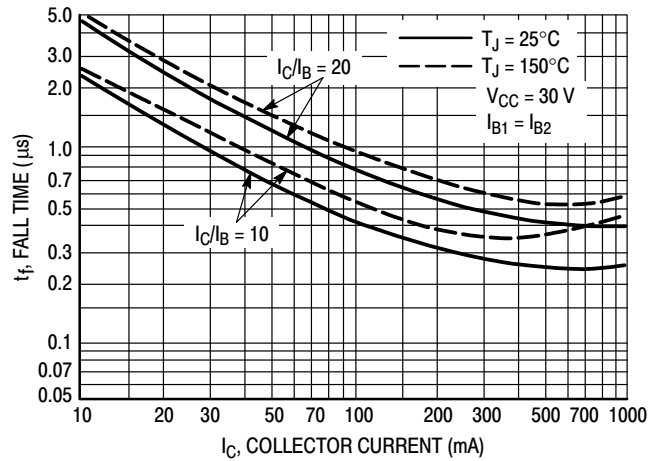


Figure 7. Fall Time

2N4918 – 2N4920 Series

TYPICAL DC CHARACTERISTICS

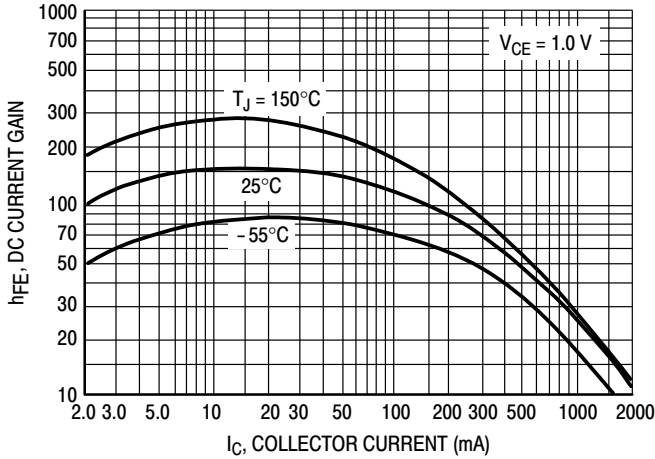


Figure 8. Current Gain

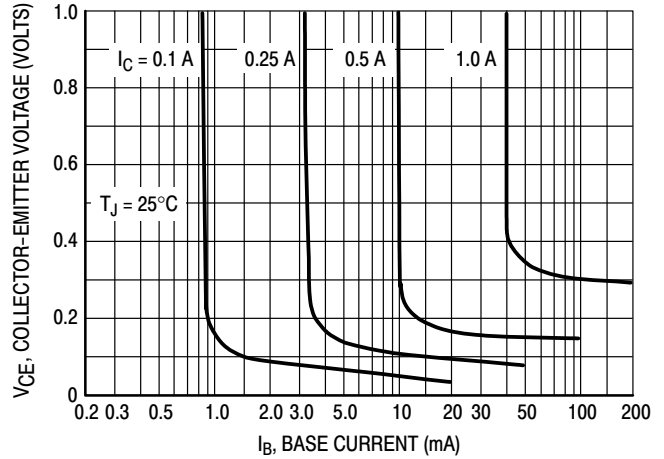


Figure 9. Collector Saturation Region

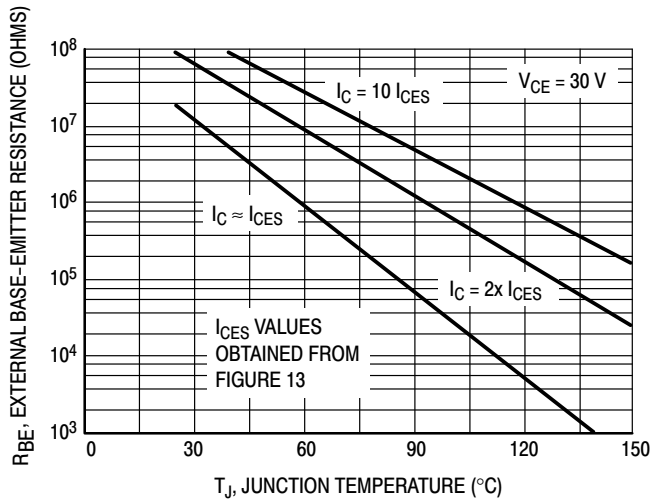


Figure 10. Effects of Base-Emitter Resistance

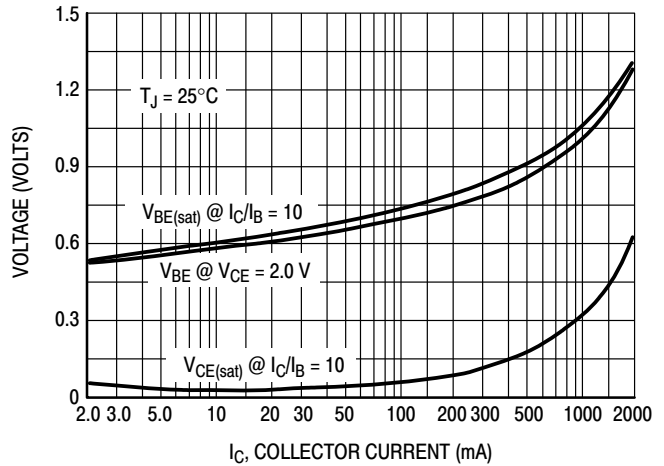


Figure 11. "On" Voltage

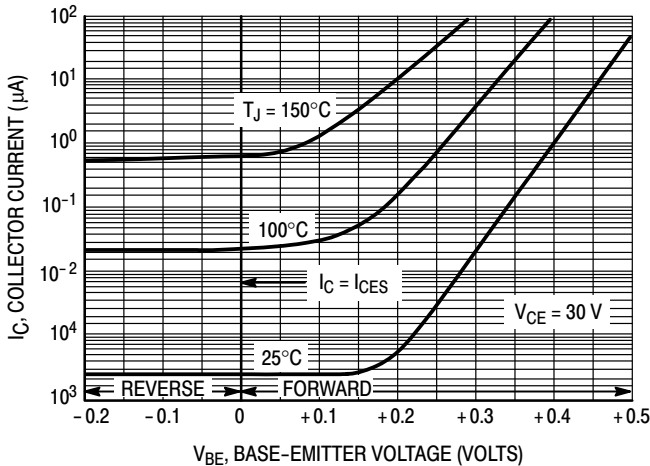


Figure 12. Collector Cut-Off Region

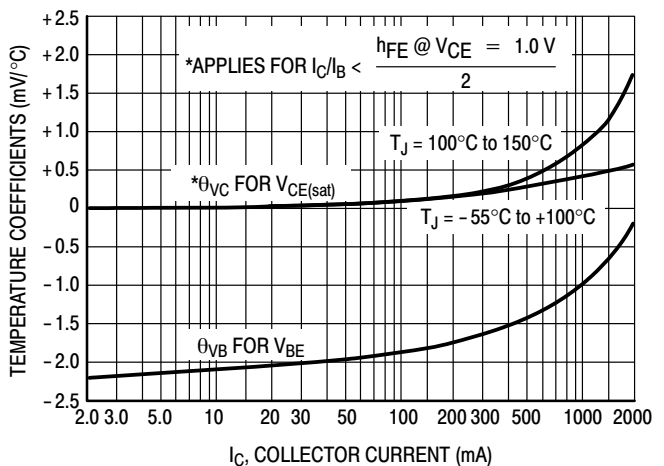
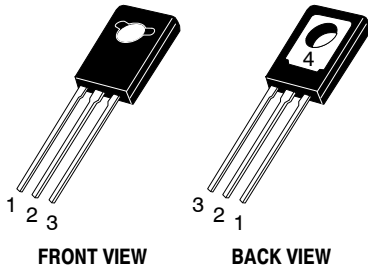


Figure 13. Temperature Coefficients

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

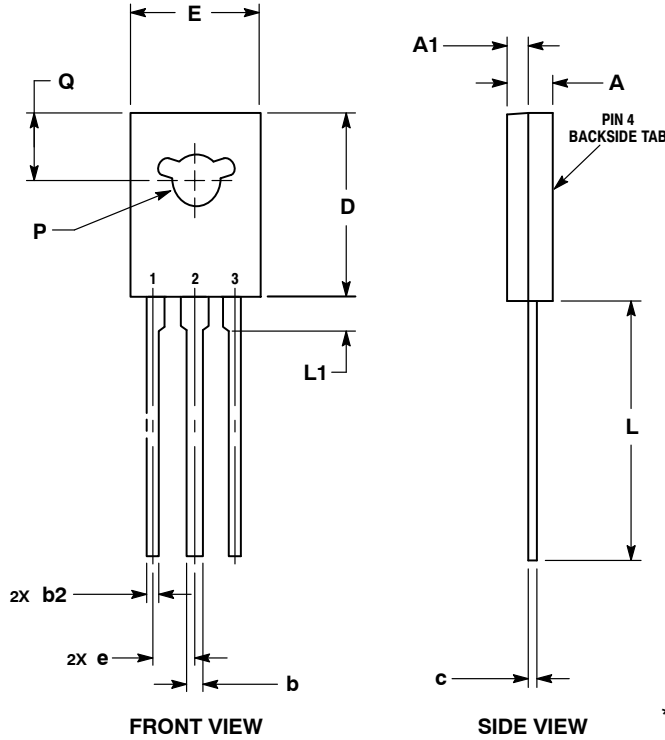
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TO-225
CASE 77-09
ISSUE AD

DATE 25 MAR 2015

SCALE 1:1

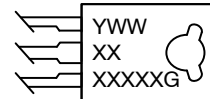


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. NUMBER AND SHAPE OF LUGS OPTIONAL.

DIM	MILLIMETERS	
	MIN	MAX
A	2.40	3.00
A1	1.00	1.50
b	0.60	0.90
b2	0.51	0.88
c	0.39	0.63
D	10.60	11.10
E	7.40	7.80
e	2.04	2.54
L	14.50	16.63
L1	1.27	2.54
P	2.90	3.30
Q	3.80	4.20

GENERIC MARKING DIAGRAM*



- Y = Year
- WW = Work Week
- XXXXX = Device Code
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "µ", may or may not be present.

- | | | | | |
|---|---|---|---|---|
| <p>STYLE 1:
PIN 1. EMITTER
2., 4. COLLECTOR
3. BASE</p> | <p>STYLE 2:
PIN 1. CATHODE
2., 4. ANODE
3. GATE</p> | <p>STYLE 3:
PIN 1. BASE
2., 4. COLLECTOR
3. EMITTER</p> | <p>STYLE 4:
PIN 1. ANODE 1
2., 4. ANODE 2
3. GATE</p> | <p>STYLE 5:
PIN 1. MT 1
2., 4. MT 2
3. GATE</p> |
| <p>STYLE 6:
PIN 1. CATHODE
2., 4. GATE
3. ANODE</p> | <p>STYLE 7:
PIN 1. MT 1
2., 4. GATE
3. MT 2</p> | <p>STYLE 8:
PIN 1. SOURCE
2., 4. GATE
3. DRAIN</p> | <p>STYLE 9:
PIN 1. GATE
2., 4. DRAIN
3. SOURCE</p> | <p>STYLE 10:
PIN 1. SOURCE
2., 4. DRAIN
3. GATE</p> |

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